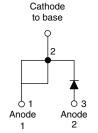


Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 8 A





TO-247AC modified

PRODUCT SUMMARY					
V _R	1200 V				
V _F at 8 A at 25 °C	3.3 V				
I _{F(AV)}	8 A				
t _{rr} (typical)	28 ns				
T _J (maximum)	150 °C				
Q _{rr} (typical)	140 nC				
dI _{(rec)M} /dt (typical) at 125 °C	85 A/μs				
I _{RRM} (typical)	4.5 A				

FEATURES

- · Ultrafast recovery
- · Ultrasoft recovery
- Very low I_{RRM}
- Very low Q_{rr}
- Specified at operating conditions
- · Lead (Pb)-free
- · Designed and qualified for industrial level

BENEFITS

- · Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- · Higher frequency operation
- Reduced snubbing
- · Reduced parts count

DESCRIPTION

HFA08PB120 is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the HFA08PB120 is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I_{RRM}) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED HFA08PB120 is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Cathode to anode voltage	V_{R}		1200	V	
Maximum continuous forward current	I _F	T _C = 100 °C	8		
Single pulse forward current	I _{FSM}		130	Α	
Maximum repetitive forward current	I _{FRM}		32		
Maximum power dissipation	P _D	T _C = 25 °C	73.5	W	
Maximum power dissipation		T _C = 100 °C	29	VV	
Operating junction and storage temperature range	T_J , T_{Stg}		- 55 to + 150	°C	

^{*} Pb containing terminations are not RoHS compliant, exemptions may apply

HFA08PB120PbF

Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	Ι _R = 100 μΑ		1200	-	-	
		I _F = 8.0 A	See fig. 1	-	2.6	3.3	V
Maximum forward voltage	V_{FM}	I _F = 16 A		-	3.4	4.3	
		I _F = 8.0 A, T _J = 125 °C		-	2.4	3.1	
Maximum reverse		$V_R = V_R$ rated	See fig. 2	-	0.31	10	
leakage current	I _{RM}	$T_J = 125 ^{\circ}\text{C}, V_R = 0.8 \text{x} V_R \text{rated}$	See lig. 2	-	135	1000	μΑ
Junction capacitance	C _T	V _R = 200 V	See fig. 3	=	11	20	pF
Series inductance	L _S	Measured lead to lead 5 mm from package body - 8.0		-	nΗ		

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
	t _{rr}	$I_F = 1.0 \text{ A}, dI_F/dt = 200 \text{ A/}\mu\text{s}, V_R = 30 \text{ V}$		-	28	-	
Reverse recovery time See fig. 5, 10	t _{rr1}	T _J = 25 °C	$I_F = 8.0 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	63	95	ns
occ lig. 5, 10	t _{rr2}	T _J = 125 °C		-	106	160	
Peak recovery current IRRM	I _{RRM1}	T _J = 25 °C		-	4.5	8.0	А
See fig. 6	I _{RRM2}	T _J = 125 °C		-	6.2	11	
Reverse recovery charge	Q _{rr1}	T _J = 25 °C		-	140	380	nC
See fig. 7	Q _{rr2}	T _J = 125 °C		-	335	880	nc
Peak rate of recovery	dI _{(rec)M} /dt1	T _J = 25 °C		-	133	-	
current during t_b See fig. 8 $dI_{(rec)M}/dt2$ $T_J = 125$ °C		-	85	-	A/μs		

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Lead temperature	T _{lead}	0.063" from case (1.6 mm) for 10 s	-	-	300	°C
Thermal resistance, junction to case	R _{thJC}		-	-	1.7	
Thermal resistance, junction to ambient	R _{thJA}	Typical socket mount	-	-	40	K/W
Thermal resistance, case to heatsink	R _{thCS}	Mounting surface, flat, smooth and greased	-	0.25	-	
Weight			-	6.0	-	g
vveigni			-	0.21	-	OZ.
Mounting torque			6.0 (5.0)	-	12 (10)	kgf · cm (lbf · in)
Marking device		Case style TO-247AC modified (JEDEC)		HFA08	3PB120	



HEXFRED® Ultrafast Soft Recovery Diode, 8 A

Vishay High Power Products

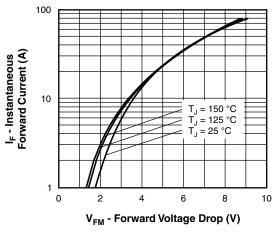


Fig. 1 - Maximum Forward Voltage Drop Characteristics

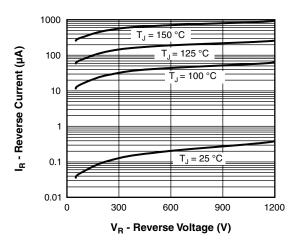


Fig. 2 - Values of Reverse Current vs.
Reverse Voltage

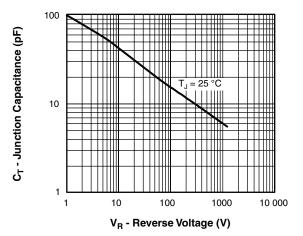


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

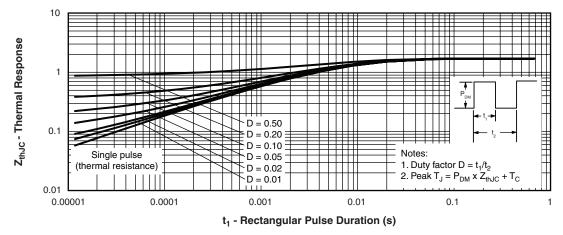


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



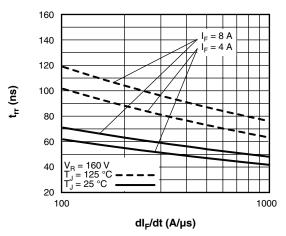


Fig. 5 - Typical Reverse Recovery Time vs. dl_F/dt

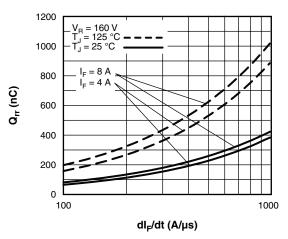


Fig. 7 - Typical Stored Charge vs. dl_F/dt

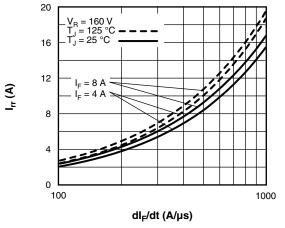


Fig. 6 - Typical Recovery Current vs. dl_F/dt

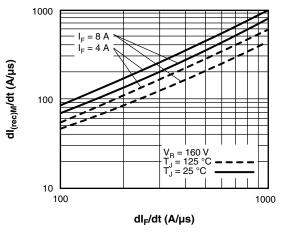


Fig. 8 - Typical $dl_{(rec)M}/dt$ vs. dl_F/dt



HEXFRED® Vishay High Power Products Ultrafast Soft Recovery Diode, 8 A

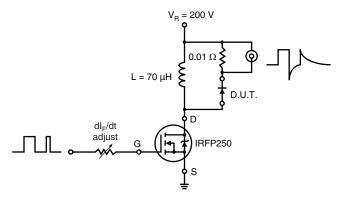
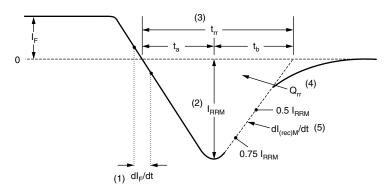


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{r}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) $\mathbf{Q}_{\rm rr}$ area under curve defined by $\mathbf{t}_{\rm rr}$ and $\mathbf{I}_{\rm RRM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $dI_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

HFA08PB120PbF

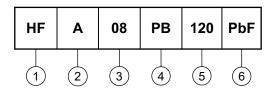
Vishay High Power Products

HEXFRED® Ultrafast Soft Recovery Diode, 8 A



ORDERING INFORMATION TABLE

Device code



1 - HEXFRED® family

2 - Process designator: A = Electron irradiated

B = Platinum diffused

3 - Current rating (08 = 8 A)

- Package outline (PB = TO-247, 2 pins)

- Voltage rating (120 = 1200 V)

None = Standard production

• PbF = Lead (Pb)-free

LINKS TO RELATED DOCUMENTS				
Dimensions http://www.vishay.com/doc?95253				
Part marking information	http://www.vishay.com/doc?95255			

Legal Disclaimer Notice



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Document Number: 91000 www.vishay.com
Revision: 11-Mar-11 1